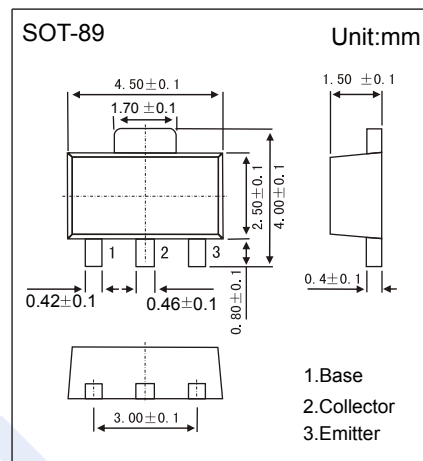


NPN Transistors

2SC3380

■ Features

- Collector Current Capability $I_C=100\text{mA}$
- Collector Emitter Voltage $V_{CEO}=300\text{V}$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	300	V
Collector - Emitter Voltage	V_{CEO}	300	
Emitter - Base Voltage	V_{EBO}	5	
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100\ \mu\text{A}, I_E = 0$	300			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1\ \text{mA}, R_{BE} = \infty$	300			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100\ \mu\text{A}, I_C = 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 300\ \text{V}, I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 250\ \text{V}, R_{BE} = \infty$			1	
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\ \text{V}, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 20\ \text{mA}, I_B = 2\ \text{mA}$			1.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 20\ \text{mA}, I_B = 2\ \text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 20\ \text{V}, I_C = 20\ \text{mA}$	30		200	
Collector output capacitance	C_{ob}	$V_{CB} = 20\ \text{V}, I_E = 0, f = 1\ \text{MHz}$			4	pF
Transition frequency	f_T	$V_{CE} = 20\ \text{V}, I_C = 20\ \text{mA}$		80		MHz

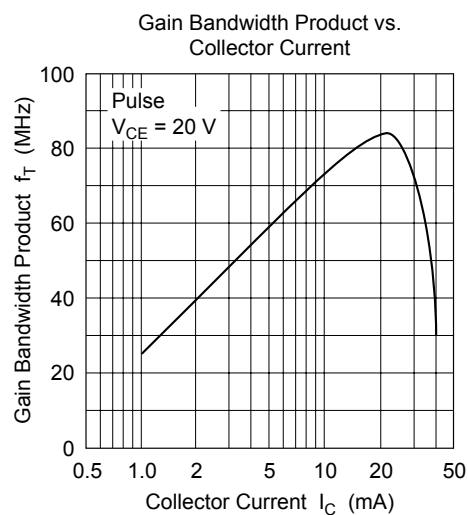
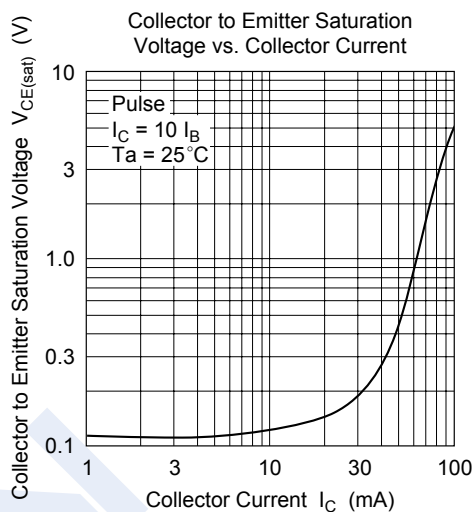
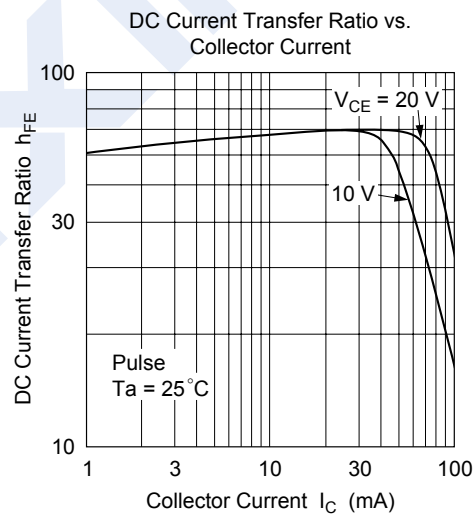
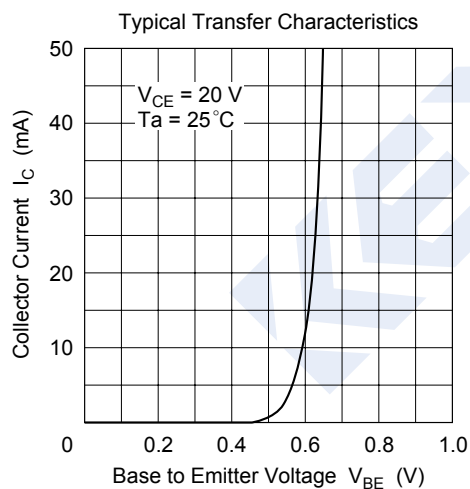
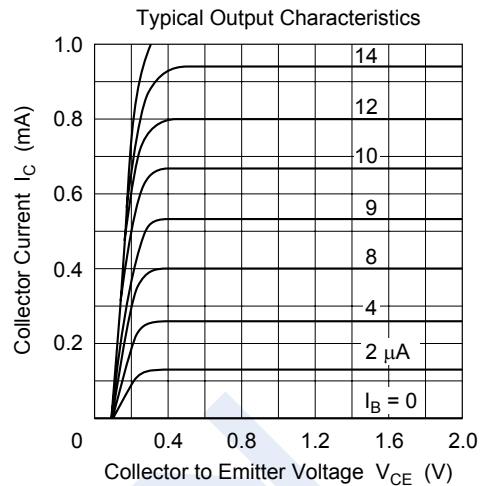
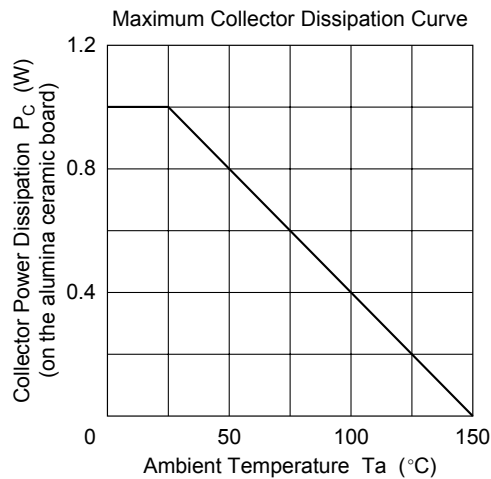
■ Marking

Marking	AS
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NPN Transistors

2SC3380

■ Typical Characteristics



NPN Transistors

2SC3380

■ Typical Characteristics

